

TOSHIBA Field Effect Transistor Silicon N Channel MOS Type (U-MOSIII)

TPCS8210

Lithium Ion Battery Applications

- Has a small footprint.
- Low drain-source ON resistance: $R_{DS(ON)} = 19\text{ m}\Omega$ (typ.)
- High forward transfer admittance: $|Y_{fs}| = 9.2\text{ S}$ (typ.)
- Low leakage current: $I_{DSS} = 10\text{ }\mu\text{A}$ (max) ($V_{DS} = 20\text{ V}$)
- Enhancement-mode: $V_{th} = 0.5\sim 1.2\text{ V}$ ($V_{DS} = 10\text{ V}$, $I_D = 200\text{ }\mu\text{A}$)
- Common drain

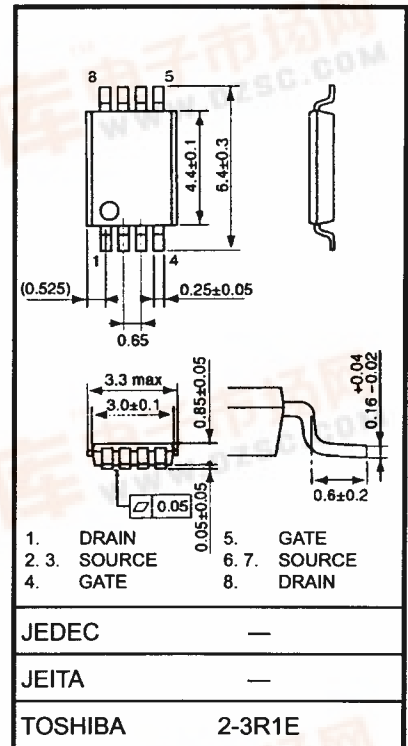
Maximum Ratings ($T_a = 25^\circ\text{C}$)

Characteristics		Symbol	Rating	Unit
Drain-source voltage		V_{DSS}	20	V
Drain-gate voltage ($R_{GS} = 20\text{ k}\Omega$)		V_{DGR}	20	V
Gate-source voltage		V_{GSS}	± 12	V
Drain current	DC (Note 1)	I_D	5	A
	Pulse (Note 1)	I_{DP}	20	
Drain power dissipation ($t = 10\text{ s}$) (Note 2a)	Single-device operation (Note 3a)	$P_D(1)$	1.1	W
	Single-device value at dual operation (Note 3b)	$P_D(2)$	0.75	
Drain power dissipation ($t = 10\text{ s}$) (Note 2b)	Single-device operation (Note 3a)	$P_D(1)$	0.6	W
	Single-device value at dual operation (Note 3b)	$P_D(2)$	0.35	
Single pulse avalanche energy (Note 4)		E_{AS}	32.5	mJ
Avalanche current		I_{AR}	5	A
Repetitive avalanche energy Single-device value at dual operation (Note 2a, 3b, 5)		E_{AR}	0.075	mJ
Channel temperature		T_{ch}	150	$^\circ\text{C}$
Storage temperature range		T_{stg}	-55~150	$^\circ\text{C}$

Note: (Note 1), (Note 2), (Note 3), (Note 4), (Note 5) Please see next page.

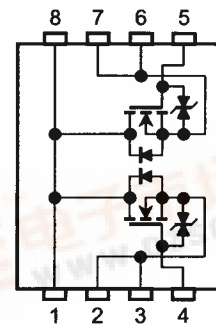
This transistor is an electrostatic sensitive device. Please handle with caution.

Unit: mm



Weight: 0.035 g (typ.)

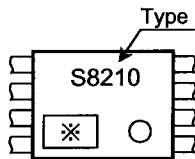
Circuit Configuration



Thermal Characteristics

Characteristics		Symbol	Max	Unit
Thermal resistance, channel to ambient (t = 10 s) (Note 2a)	Single-device operation (Note 3a)	$R_{th(ch-a)}(1)$	114	°C/W
	Single-device value at dual operation (Note 3b)	$R_{th(ch-a)}(2)$	167	
Thermal resistance, channel to ambient (t = 10 s) (Note 2b)	Single-device operation (Note 3a)	$R_{th(ch-a)}(1)$	208	°C/W
	Single-device value at dual operation (Note 3b)	$R_{th(ch-a)}(2)$	357	

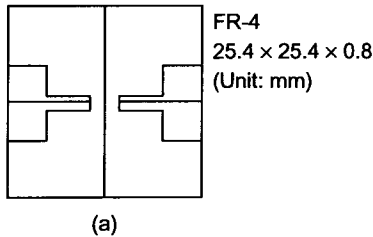
Marking (Note 6)



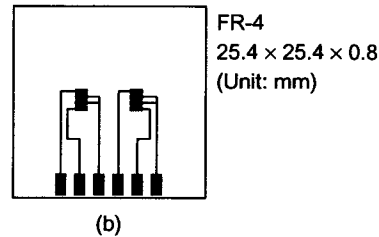
Note 1: The channel temperature should not exceed 150°C.

Note 2:

a) Device mounted on a glass-epoxy board (a)



b) Device mounted on a glass-epoxy board (b)



Note 3:

- a) The power dissipation and thermal resistance values are shown for a single device (During single-device operation, power is only applied to one device.).
- b) The power dissipation and thermal resistance values are shown for a single device (During dual operation, power is evenly applied to both devices.).

Note 4: $V_{DD} = 16\text{ V}$, $T_{ch} = 25^\circ\text{C}$ (initial), $L = 1.0\text{ mH}$, $R_G = 25\ \Omega$, $I_{AR} = 5\text{ A}$

Note 5: Repetitive rating; pulse width limited by max channel temperature.

Note 6: o on lower right of the marking indicates Pin 1.

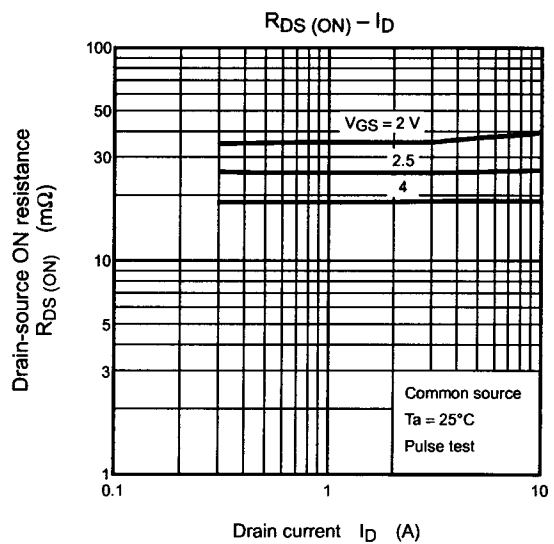
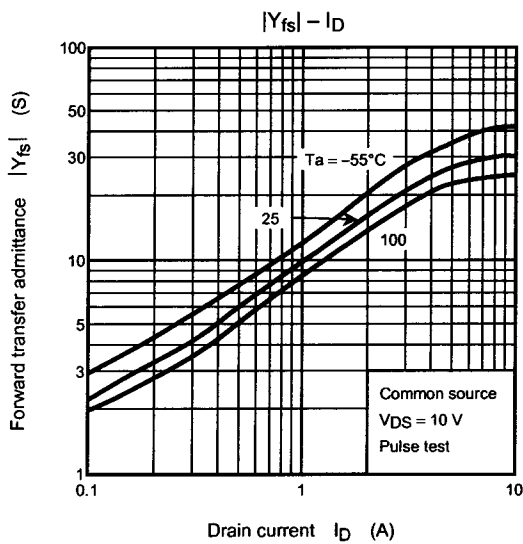
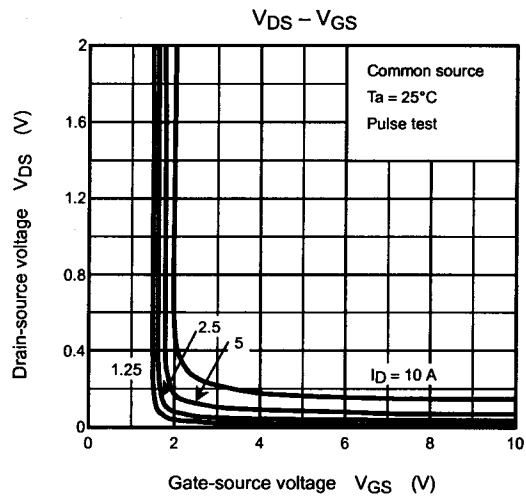
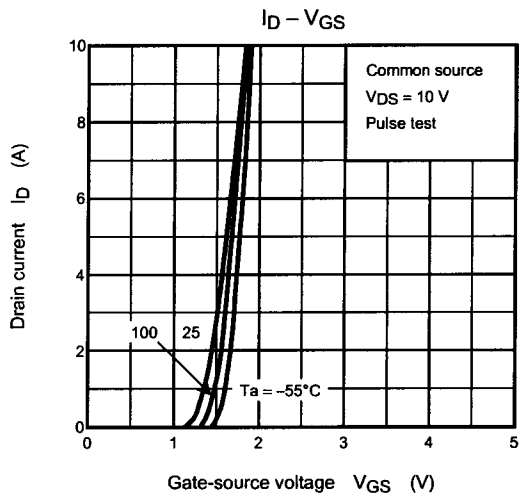
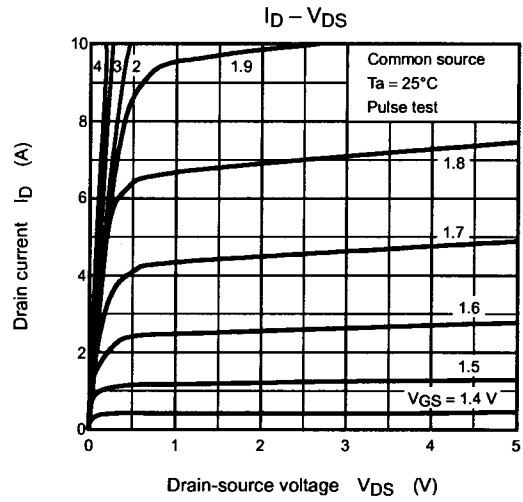
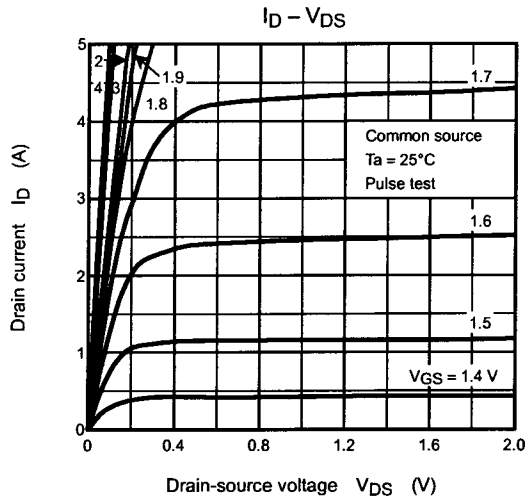
* shows lot number. (Year of manufacture: last decimal digit of the year of manufacture, Month of manufacture: January to December are denoted by letters A to L respectively)

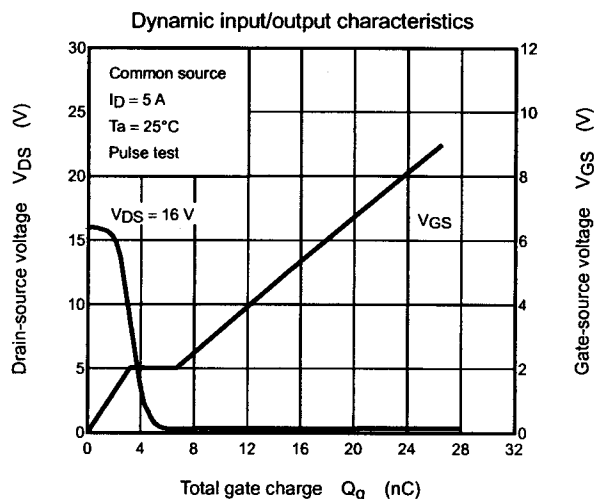
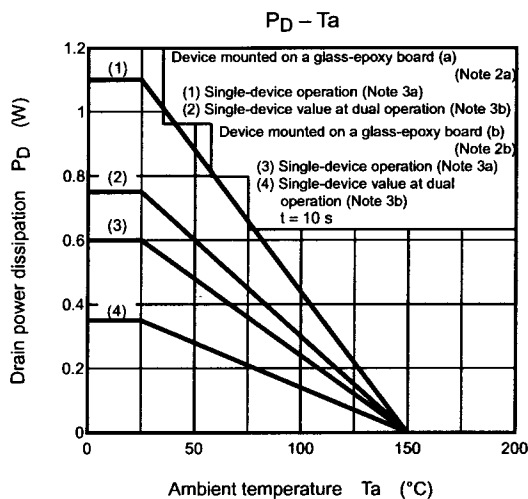
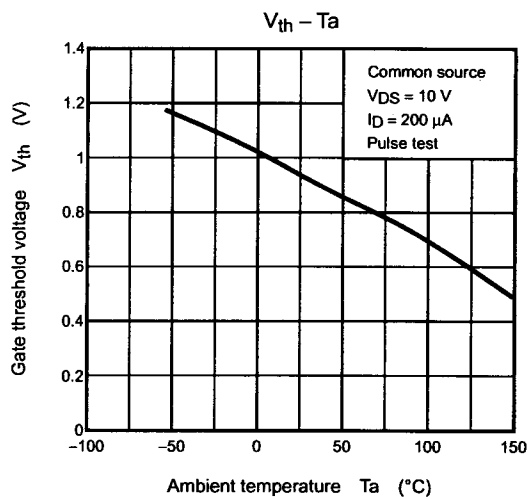
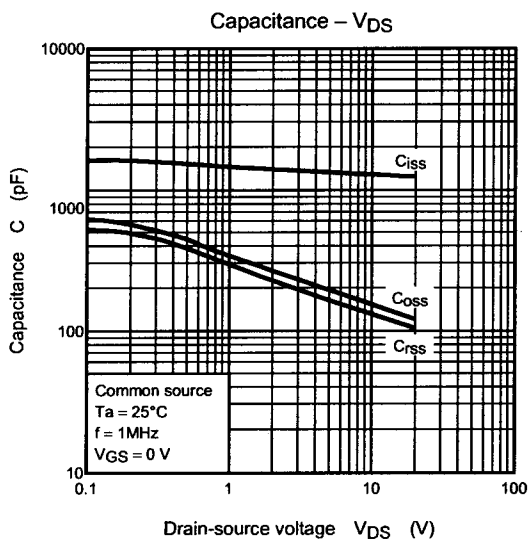
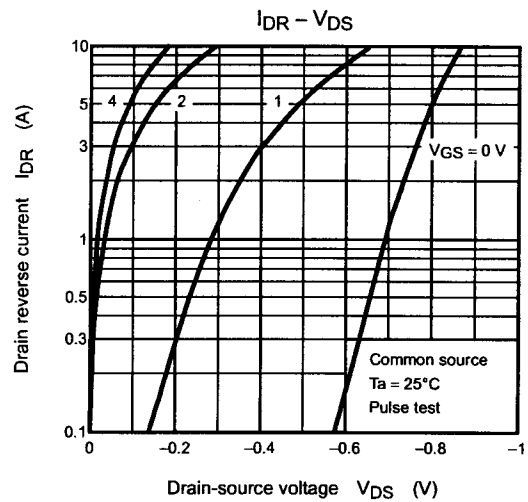
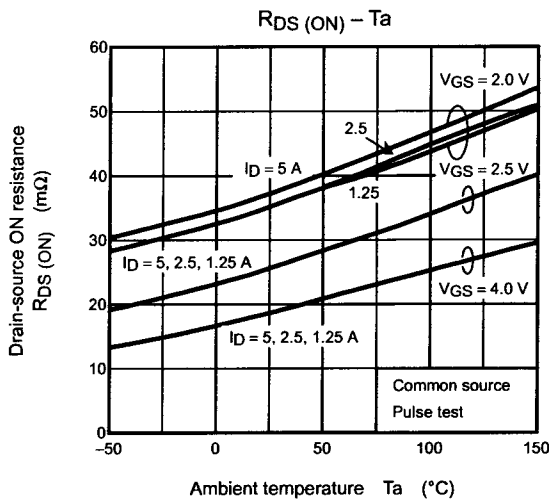
Electrical Characteristics (Ta = 25°C)

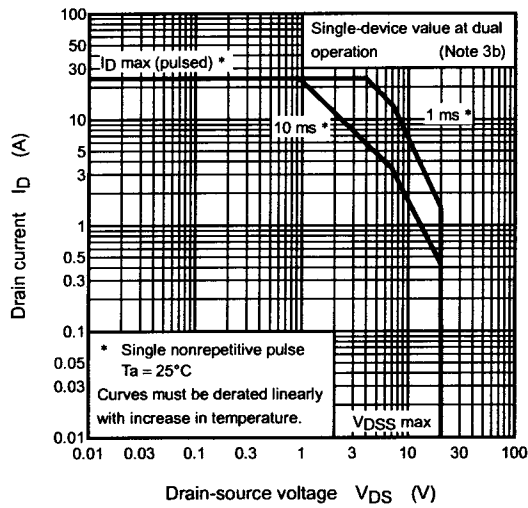
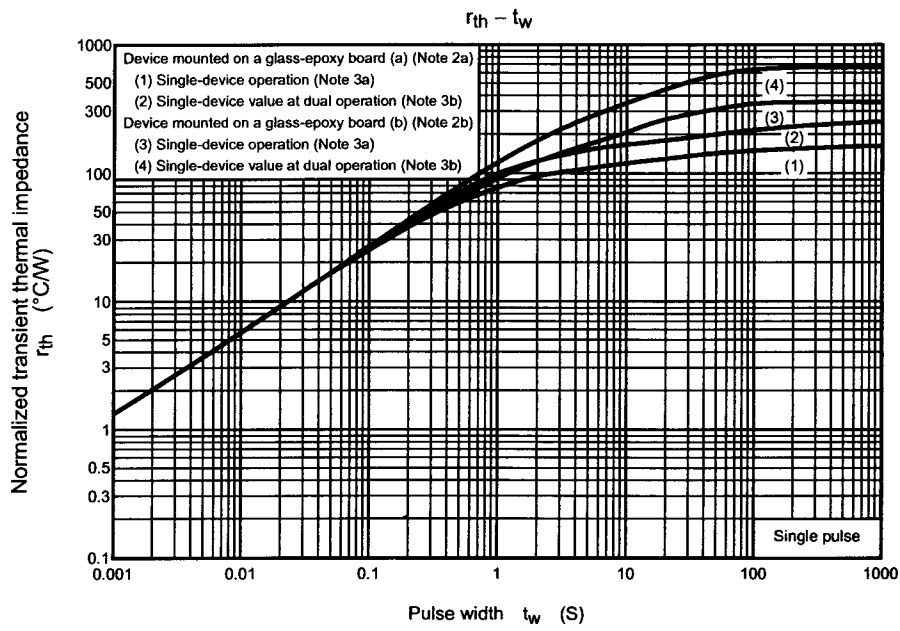
Characteristics		Symbol	Test Condition	Min	Typ.	Max	Unit
Gate leakage current		I_{GSS}	$V_{GS} = \pm 10\text{ V}, V_{DS} = 0\text{ V}$	—	—	± 10	μA
Drain cut-OFF current		I_{DSS}	$V_{DS} = 20\text{ V}, V_{GS} = 0\text{ V}$	—	—	10	μA
Drain-source breakdown voltage		$V_{(BR)DSS}$	$I_D = 10\text{ mA}, V_{GS} = 0\text{ V}$	20	—	—	V
		$V_{(BR)DSX}$	$I_D = 10\text{ mA}, V_{GS} = -12\text{ V}$	8	—	—	
Gate threshold voltage		V_{th}	$V_{DS} = 10\text{ V}, I_D = 200\ \mu\text{A}$	0.5	—	1.2	V
Drain-source ON resistance		$R_{DS(ON)}$	$V_{GS} = 2.0\text{ V}, I_D = 3.5\text{ A}$	—	34	60	m Ω
			$V_{GS} = 2.5\text{ V}, I_D = 3.5\text{ A}$	—	26	40	
			$V_{GS} = 4.0\text{ V}, I_D = 4.0\text{ A}$	—	19	30	
Forward transfer admittance		$ Y_{fs} $	$V_{DS} = 10\text{ V}, I_D = 2.5\text{ A}$	4.6	9.2	—	S
Input capacitance		C_{iss}	$V_{DS} = 10\text{ V}, V_{GS} = 0\text{ V}, f = 1\text{ MHz}$	—	1280	—	pF
Reverse transfer capacitance		C_{rss}		—	130	—	
Output capacitance		C_{oss}		—	150	—	
Switching time	Rise time	t_r	<p>$V_{GS} = 5\text{ V}, 0\text{ V}$ $I_D = 2.5\text{ A}$ $V_{DD} = 10\text{ V}$ $R_L = 4\ \Omega$ $4.7\ \Omega$ V_{OUT} $Duty \leq 1\%, t_w = 10\ \mu\text{s}$</p>	—	4.5	—	ns
	Turn-ON time	t_{on}		—	11	—	
	Fall time	t_f		—	7.3	—	
	Turn-OFF time	t_{off}		—	33	—	
Total gate charge (gate-source plus gate-drain)		Q_g	$V_{DD} = 16\text{ V}, V_{GS} = 5\text{ V}, I_D = 5\text{ A}$	—	15	—	nC
Gate-source charge 1		Q_{gs1}		—	3.3	—	
Gate-drain ("miller") charge		Q_{gd}		—	3.5	—	

Source-Drain Diode Ratings and Characteristics (Ta = 25°C)

Characteristics		Symbol	Test Condition	Min	Typ.	Max	Unit
Drain reverse current	Pulse (Note 1)	I_{DRP}	—	—	—	20	A
Diode forward voltage		V_{DSF}	$I_{DR} = 5\text{ A}, V_{GS} = 0\text{ V}$	—	—	-1.2	V







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